<u>Voltage Regulator</u> - High Accuracy, Very Low Dropout, Bias Rail, CMOS

150 mA

The NCP121 is a high accuracy 150 mA VLDO equipped with NMOS pass transistor and a separate bias supply voltage (V_{BIAS}). The device provides stable, very accurate output voltage with low noise suitable for space constrained, noise sensitive applications. In order to optimize performance for battery operated portable applications, the NCP121 features low I_Q consumption. The XDFN6 1.2 mm x 1.2 mm package is optimized for use in space constrained applications.

Features

- Input Voltage Range: 0.8 V to 5.5 V
 Bias Voltage Range: 2.4 V to 5.5 V
- Fixed Output Voltage Device
- Output Voltage Range: 0.8 V to 2.1 V
- $\pm 1.0\%$ Accuracy over Line, Load and Temperature, 0.2% V_{OUT} @ $25^{\circ}C$
- Ultra-Low Dropout: 75 mV Maximum at 150 mA
- Very Low Bias Input Current of Typ. 80 μA
- Very Low Bias Input Current in Disable Mode: Typ. 0.5 μA
- Logic Level Enable Input for ON/OFF control
- Output Active Discharge Option available
- Stable with a 1 μF Ceramic Capacitor
- Available in XDFN6 1.2 mm x 1.2 mm x 0.4 mm package
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Battery-powered Equipment
- Smartphones, Tablets
- Cameras, DVRs, STB and Camcorders

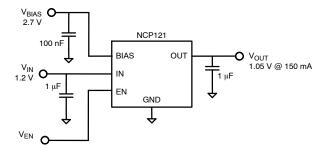


Figure 1. Typical Application Schematics



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MARKING DIAGRAM

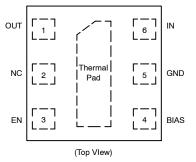


XDFN6 CASE 711AT



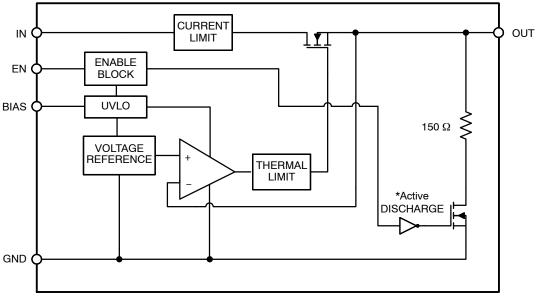
XX = Specific Device Code M = Date Code

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 7 of this data sheet.



^{*}Active output discharge function is present only in NCP121AMXyyyTCG devices. yyy denotes the particular output voltage option.

Figure 2. Simplified Schematic Block Diagram

PIN FUNCTION DESCRIPTION

Pin No.	Pin Name	Description
1	OUT	Regulated Output Voltage pin
2	N/C	Not internally connected
3	EN	Enable pin. Driving this pin high enables the regulator. Driving this pin low puts the regulator into shutdown mode.
4	BIAS	Bias voltage supply for internal control circuits. This pin is monitored by internal Under-Voltage Lockout Circuit.
5	GND	Ground pin
6	IN	Input Voltage Supply pin
Pad		Should be soldered to the ground plane for increased thermal performance.

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Input Voltage (Note 1)	V _{IN}	-0.3 to 6	V
Output Voltage	V _{OUT}	-0.3 to $(V_{IN}+0.3) \le 6$	V
Chip Enable and Bias Input	V _{EN} , V _{BIAS}	-0.3 to 6	V
Output Short Circuit Duration	t _{SC}	unlimited	s
Maximum Junction Temperature	TJ	150	°C
Storage Temperature	T _{STG}	-55 to 150	°C
ESD Capability, Human Body Model (Note 2)	ESD _{HBM}	2000	V
ESD Capability, Machine Model (Note 2)	ESD _{MM}	200	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.
- 2. This device series incorporates ESD protection (except OUT pin) and is tested by the following methods:
 - ESD Human Body Model tested per EIA/JESD22-A114
 - ESD Machine Model tested per EIA/JESD22-A115
 - Latchup Current Maximum Rating tested per JEDEC standard: JESD78.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Characteristics, XDFN6 1.2 mm x 1.2 mm Thermal Resistance, Junction-to-Air	$R_{ heta JA}$	170	°C/W

ELECTRICAL CHARACTERISTICS

 $-40^{\circ}\text{C} \le \text{T}_{J} \le 85^{\circ}\text{C}$; $\text{V}_{\text{BIAS}} = 2.7 \text{ V or } (\text{V}_{\text{OUT}} + 1.6 \text{ V})$, whichever is greater, $\text{V}_{\text{IN}} = \text{V}_{\text{OUT}(\text{NOM})} + 0.3 \text{ V}$, $\text{I}_{\text{OUT}} = 1 \text{ mA}$, $\text{V}_{\text{EN}} = 1 \text{ V}$, unless otherwise noted. $\text{C}_{\text{IN}} = 1 \text{ } \mu\text{F}$, $\text{C}_{\text{BIAS}} = 0.1 \text{ } \mu\text{F}$, $\text{C}_{\text{OUT}} = 1 \text{ } \mu\text{F}$ (effective capacitance) (Note 3). Typical values are at $\text{T}_{J} = +25^{\circ}\text{C}$. Min/Max values are for $-40^{\circ}\text{C} \le \text{T}_{J} \le 85^{\circ}\text{C}$ unless otherwise noted. (Note 4)

Parameter	Test Conditions	Symbol	Min	Тур	Max	Unit
Operating Input Voltage Range		V _{IN}	V _{OUT} +V _{DO}		5.5	V
Operating Bias Voltage Range		V_{BIAS}	(V _{OUT} +1.35) ≥2.4		5.5	V
Undervoltage Lock-out	V _{BIAS} Rising Hysteresis	UVLO		1.6 0.2		٧
Output Voltage Accuracy	$-40^{\circ}C \leq T_{J} \leq 85^{\circ}C,~V_{OUT(NOM)} + 0.3~V \leq V_{IN} \leq 5.0~V,~2.7~V~or~(V_{OUT(NOM)} + 1.6~V),~whichever~is~greater~<~V_{BIAS} < 5.5~V,~1~mA < I_{OUT} < 150~mA$	V _{OUT}	-1.0		+1.0	%
Output Voltage Accuracy		V _{OUT}		±0.2		%
V _{IN} Line Regulation	$V_{OUT(NOM)} + 0.3 \text{ V} \le V_{IN} \le 5.0 \text{ V}$	Line _{Reg}		0.01		%/V
V _{BIAS} Line Regulation	2.7 V or (V _{OUT(NOM)} + 1.6 V), whichever is greater < V _{BIAS} < 5.5 V	Line _{Reg}		0.01		%/V
Load Regulation	I _{OUT} = 1 mA to 150 mA	Load _{Reg}		1.5		mV
V _{IN} Dropout Voltage	I _{OUT} = 150 mA (Note 5)	V_{DO}		37	75	mV
V _{BIAS} Dropout Voltage	I _{OUT} = 150 mA, V _{IN} = V _{BIAS} (Note 5)	V_{DO}		1.1	1.4	V
Output Current Limit	V _{OUT} = 90% V _{OUT(NOM)}	I _{CL}	200	330	600	mA
Bias Pin Operating Current	V _{BIAS} = 2.7 V	I _{BIAS}		80	110	μΑ
Bias Pin Disable Current	V _{EN} ≤ 0.4 V	I _{BIAS(DIS)}		0.5	1	μΑ
Vinput Pin Disable Current	V _{EN} ≤ 0.4 V	I _{VIN(DIS)}		0.5	1	μΑ
EN Pin Threshold	EN Input Voltage "H"	V _{EN(H)}	0.9			V
Voltage	EN Input Voltage "L"	V _{EN(L)}			0.4	
EN Pull Down Current	V _{EN} = 5.5 V	I _{EN}		0.3	1.0	μΑ
Turn-On Time	C_{OUT} = 1 μ F, From assertion of V_{EN} to V_{OUT} = 98% $V_{OUT(NOM)}$, $V_{OUT(NOM)}$ = 1.05 V	t _{ON}		150		μs
Power Supply Rejection Ratio	V_{IN} to V_{OUT} , f = 1 kHz, I_{OUT} = 150 mA, $V_{IN} \ge V_{OUT}$ +0.5 V	PSRR(V _{IN})		70		dB
	V_{BIAS} to V_{OUT} , f = 1 kHz, I_{OUT} = 150 mA, $VIN \ge V_{OUT}$ +0.5 V	PSRR(V _{BIAS})		80		dB
Output Noise Voltage	$V_{IN} = V_{OUT} + 0.5 \text{ V}, V_{OUT(NOM)} = 1.05 \text{ V},$ f = 10 Hz to 100 kHz	V _N		40		μV _{RMS}
Thermal Shutdown	Temperature increasing			160		°C
Threshold	Temperature decreasing			140		1
Output Discharge Pull-Down	$V_{EN} \le 0.4 \text{ V}, V_{OUT} = 0.5 \text{ V},$ NCP121A options only	R _{DISCH}		150		Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{3.} Effective capacitance, including the effect of DC bias, tolerance and temperature. See the Application Information section for more information.

Performance guaranteed over the indicated operating temperature range by design and/or characterization. Production tested at T_A = 25°C.
 Low duty cycle pulse techniques are used during the testing to maintain the junction temperature as close to ambient as possible.

^{5.} Dropout voltage is characterized when V_{OUT} falls 3% below V_{OUT(NOM)}.

APPLICATIONS INFORMATION

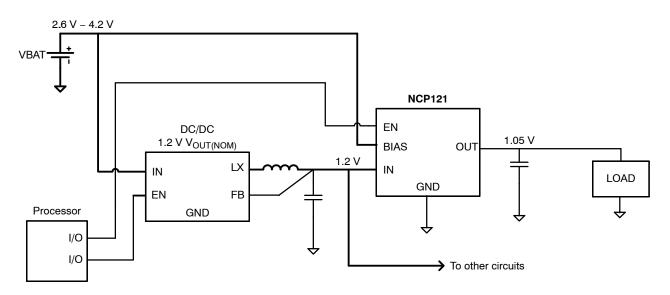
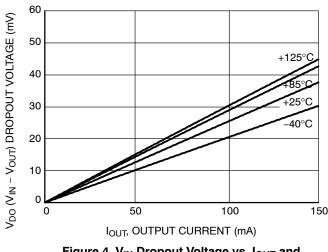


Figure 3. Typical Application: Low-Voltage Post-Regulator with ON/OFF functionality

TYPICAL CHARACTERISTICS

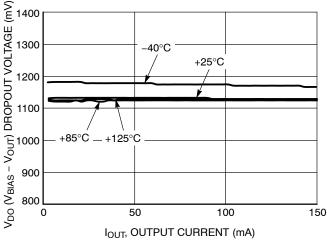
At T_J = +25°C, V_{IN} = $V_{OUT(TYP)}$ + 0.3 V, V_{BIAS} = 2.7 V, V_{EN} = V_{BIAS} , $V_{OUT(NOM)}$ = 1.05 V, I_{OUT} = 150 mA, C_{IN} = 1 μ F, C_{BIAS} = 0.1 μ F, and C_{OUT} = 1 μ F (effective capacitance), unless otherwise noted.



200 V_{DO} (V_{IN} - V_{OUT}) DROPOUT VOLTAGE (mV) I_{OUT} = 150 mA 180 160 140 120 100 80 +125°C +85°C +25°C 60 -40°C 40 20 0.5 1.0 2.0 2.5 3.0 4.5 1.5 3.5 4.0 V_{BIAS} - V_{OUT} (V)

Figure 4. V_{IN} Dropout Voltage vs. I_{OUT} and Temperature T_J

Figure 5. V_{IN} Dropout Voltage vs. (V_{BIAS} – V_{OUT}) and Temperature T_J



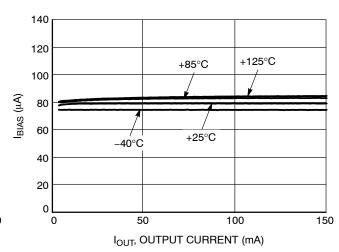
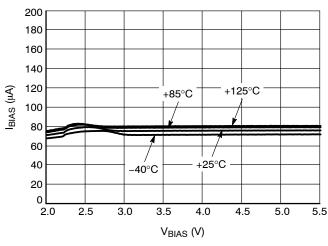


Figure 6. V_{BIAS} Dropout Voltage vs. I_{OUT} and Temperature T_J

Figure 7. BIAS Pin Current vs. I_{OUT} and Temperature T_J



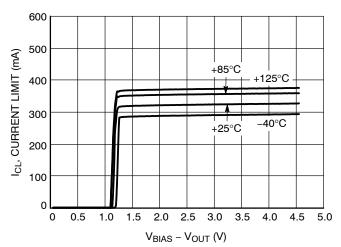


Figure 8. BIAS Pin Current vs. V_{BIAS} and Temperature T_J

Figure 9. Current Limit vs. (V_{BIAS} - V_{OUT})

APPLICATIONS INFORMATION

The NCP121 dual–rail very low dropout voltage regulator is using NMOS pass transistor for output voltage regulation from $V_{\rm IN}$ voltage. All the low current internal controll circuitry is powered from the $V_{\rm BIAS}$ voltage.

The use of an NMOS pass transistor offers several advantages in applications. Unlike a PMOS topology devices, the output capacitor has reduced impact on loop stability. V_{IN} to V_{OUT} operating voltage difference can be very low compared with standard PMOS regulators in very low V_{IN} applications.

The NCP121 offers smooth monotonic start-up. The controlled voltage rising limits the inrush current.

The Enable (EN) input is equipped with internal hysteresis.

NCP121 is a Fixed Voltage linear regulator.

Dropout Voltage

Because of two power supply inputs V_{IN} and V_{BIAS} and one V_{OUT} regulator output, there are two Dropout voltages specified.

The first, the V_{IN} Dropout voltage is the voltage difference $(V_{IN}-V_{OUT})$ when V_{OUT} starts to decrease by percents specified in the Electrical Characteristics table. V_{BIAS} is high enough, specific value is published in the Electrical Characteristics table.

The second, V_{BIAS} dropout voltage is the voltage difference ($V_{BIAS} - V_{OUT}$) when V_{IN} and V_{BIAS} pins are joined together and V_{OUT} starts to decrease.

Input and Output Capacitors

The device is designed to be stable for ceramic output capacitors with Effective capacitance in the range from $1\,\mu F$ to $10\,\mu F$. The device is also stable with multiple capacitors in parallel, having the total effective capacitance in the specified range.

In applications where no low input supplies impedance available (PCB inductance in V_{IN} and/or V_{BIAS} inputs as example), the recommended C_{IN} = 1 μF and C_{BIAS} = 0.1 μF or greater. Ceramic capacitors are recommended. For the best performance all the capacitors should be connected to the NCP121 respective pins directly in the device PCB copper layer, not through vias having not negligible impedance.

When using small ceramic capacitor, their capacitance is not constant but varies with applied DC biasing voltage, temperature and tolerance. The effective capacitance can be much lower than their nominal capacitance value, most importantly in negative temperatures and higher LDO output voltages. That is why the recommended Output capacitor capacitance value is specified as Effective value in the specific application conditions.

Enable Operation

The enable pin will turn the regulator on or off. The threshold limits are covered in the electrical characteristics table in this data sheet. If the enable function is not to be used then the pin should be connected to $V_{\rm IN}$ or $V_{\rm BIAS}$.

Current Limitation

The internal Current Limitation circuitry allows the device to supply the full nominal current and surges but protects the device against Current Overload or Short.

Thermal Protection

Internal thermal shutdown (TSD) circuitry is provided to protect the integrated circuit in the event that the maximum junction temperature is exceeded. When TSD activated, the regulator output turns off. When cooling down under the low temperature threshold, device output is activated again. This TSD feature is provided to prevent failures from accidental overheating.

ORDERING INFORMATION

Device	Nominal Output Voltage	Marking	Marking Rotation	Option	Package	Shipping [†]	
NCP121AMX140TCG	1.40 V	V	90°				
NCP121AMX145TCG	1.45 V	Υ	90°				
NCP121AMX160TCG	1.60 V	2	90°		XDFN6 (Pb-Free)	0000 /T 0 P1	
NCP121AMX165TCG	1.65 V	3	90°	O to the state of Disable on a			
NCP121AMX170TCG	1.70 V	4	90°	Output Active Discharge		3000 / Tape & Reel	
NCP121AMX173TCG	1.73 V	6	180°				
NCP121AMX175TCG	1.75 V	5	90°				
NCP121AMX185TCG	1.85 V	6	90°				

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

To order other package and voltage variants, please contact your ON sales representative



PIN ONE

REFERENCE

0.05 С

6X L

DETAIL A

С

△ 0.05

NOTE 4

D

TOP VIEW

SIDE VIEW

D2

BOTTOM VIEW

В

Ε

SEATING PLANE

 \oplus 0.10 \oplus C A B

NOTE 3

C

6x L1



XDFN6 1.20x1.20, 0.40P CASE 711AT ISSUE C

DETAIL A OPTIONAL CONSTRUCTION **DATE 04 DEC 2015**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION b APPLIES TO THE PLATED TECHNINALS.
 - TERMINALS.
 COPLANARITY APPLIES TO THE PAD AS WELL AS THE TERMINALS.

	MILLIMETERS							
DIM	MIN TYP MAX							
Α	0.30	0.37	0.45					
A1	0.00 0.03 0.0							
b	0.13 0.18 0.23							
D	1.15	1.20	1.25					
D2	0.84	0.94	1.04					
E	1.15	1.20	1.25					
E2	0.20	0.30	0.40					
е	0.40 BSC							
L	0.15	0.20	0.25					
L1	0.00	0.05	0.10					

GENERIC MARKING DIAGRAM*

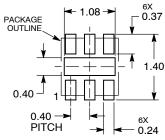


XX = Specific Device Code

= Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " • ", may or may not be present.

RECOMMENDED MOUNTING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	XDFN6, 1.20 X 1.20, 0.40P		PAGE 1 OF 1		

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